

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	100	min near tai.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	116	wang near po.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	1571	438/3.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	2152	((mtj) or (magnetic near tunnel near junction))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	401	((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
6	BRS	L6	167	((mtj) or (magnetic near tunnel near junction)) near5 (cell) near25 (wafer or substrate)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
7	BRS	L7	167	((mtj) or (magnetic near tunnel near junction)) near5 (cell) near25 (wafer or substrate)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B
8	BRS	L8	10	7 and (shiel\$3)	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	0	((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) near45 (shile\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	27	((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) near45 (shiel\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	209	((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) near45 (magnetic\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	212	((mtj) or (magnetic near tunnel near junction)) near25 (wafer or substrate) near45 (magneti\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	71944	((mtj) or (magnet\$5)) near25 (wafer or substrate) near45 (magneti\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	71251	((mtj) or (magnet\$2)) near25 (wafer or substrate) near45 (magneti\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	71251	((mtj) or (magnet\$2)) near25 ((wafer or substrate))) near45 (magneti\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	96651	((mtj) or (magnet\$2)) near25 ((wafer or substrate)))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

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17	BRS	L17	65789	((mtj) or (magnet\$2)) near5 ((wafer or substrate)))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	96651	((mtj) or (magnet\$2)) near25 ((wafer or substrate)))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	118	((((mtj) or (magnet\$2)) near (cell)) near25 ((wafer or substrate)))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	108	((magnetic near memory) near (cell)) near25 ((wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	0	((magnetic-memory) near (cell)) near25 ((wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	23	(magnetic\$3 near3 shield\$2) near35 (mtj)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	33	(magnetic\$3 near3 shield\$2) near35 (magnetic near tunnel\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20050059170 A1	Magnetic random access memory designs with patterned and stabilized magnetic shields
2			US 20050059170 A1	Magnetic random access memory designs with patterned and stabilized magnetic shields
3			US 20050045971 A1	Magnetic memory with self-aligned magnetic keeper structure
4			US 20040174756 A1	Magnetic memory device and magnetic substrate
5			US 20030210591 A1	Magnetic memory device and magnetic substrate
6			US 20030156449 A1	Thin film magnetic memory device having communication function, and distribution management system and manufacturing step management system each using thereof
7			US 20020145902 A1	Magnetic memory device and magnetic substrate
8			US 6795339 B2	Thin film magnetic memory device having communication function, and distribution management system and manufacturing step management system each using thereof
9			US 6741495 B2	Magnetic memory device and magnetic substrate
10			US 6567299 B2	Magnetic memory device and magnetic substrate